



Solid State Devices, Inc.

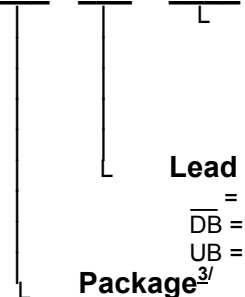
14701 Firestone Blvd * La Mirada, CA 90638
 Phone: (562) 404-4474 * Fax: (562) 404-1773
 ssdi@ssdi-power.com * www.ssdi-power.com

SFF110P05J
SFF110P05M
SFF110P05S1

DESIGNER'S DATA SHEET

Part Number / Ordering Information^{1/}

SFF110P05



Screening^{2/}
 — = Not Screened
 TX = TX Level
 TXV = TXV Level
 S = S Level

Lead Option
 — = Straight Leads
 DB = Down Bend
 UB = Up Bend

Package^{3/}
 M = TO-254
 J = TO-257
 S1 = SMD1

RADIATION TOLERANT
110 AMP , 50 Volts, 14 mΩ
Avalanche Rated P-MOSFET

- Features:**
- Rugged Trench Technology
 - Lowest ON-resistance in the industry: 10mΩ typ
 - Radiation tolerant: less than 0.5V typical gate threshold shift @ TID= 100kRAD
 - SEU and SEGR resistant to LET 38
 - Avalanche rated
 - Hermetically Sealed Power Packaging
 - Low Total Gate Charge

Maximum Ratings		Symbol	Value	Units
Drain - Source Voltage		V _{DSS}	-50	V
Gate - Source Voltage	continuous transient	V _{GS}	±20 ±30	V
Max. Continuous Drain Current (package limited) @ 25°C	TO-257 TO-254 SMD1	I _{D1}	30 55 85	A
Max. Instantaneous Drain Current (T _j limited) T _c = 25°C	TO-257, TO-254 SMD1	I _{D2} I _{D3}	80 110	A
Max. Avalanche current	@ L = 0.1 mH	I _{AS}	70	A
Single Pulse Avalanche Energy	@ L = 0.1 mH	E _{AS}	1000	mJ
Total Power Dissipation @ T _c = 25°C	TO-257, TO-254 SMD1	P _D	90 125	W
Operating & Storage Temperature		T _{OP} & T _{STG}	-55 to +150	°C
Maximum Thermal Resistance (Junction to Case)	TO-257, TO-254 SMD1	R _{θJC}	1.4 1 (typ.0.5)	°C/W

NOTES:

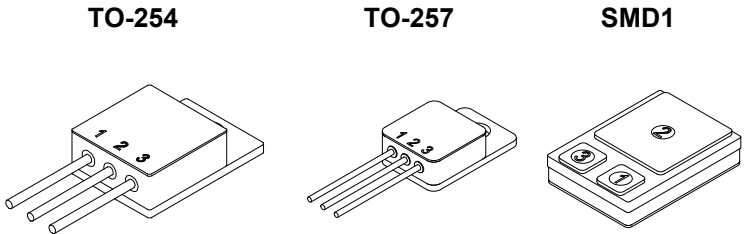
*Pulse Test: Pulse Width = 300µsec, Duty Cycle = 2%.

1/ For ordering information, price, and availability - contact factory.

2/ Screening based on MIL-PRF-19500. Screening flows available on request.

3/ Maximum current limited by package configuration

4/ Unless otherwise specified, all electrical characteristics @25°C.





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Electrical Characteristics ^{4/}		Symbol	Min	Typ	Max	Units
Drain to Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	-50	—	—	V
Drain to Source On State Resistance	$V_{GS} = -10V, I_D = -70A, T_j = 25^\circ C$	$R_{DS(on)}$	—	9	14	mΩ
	$V_{GS} = 10V, I_D = -70A, T_j = 125^\circ C$		—	14	22	
	$V_{GS} = 10V, I_D = -70A, T_j = 150^\circ C$		—	15	—	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -0.25mA, T_j = 25^\circ C$	$V_{GS(th)}$	-2.0	—	-4.0	V
	$V_{DS} = V_{GS}, I_D = 1.0mA, T_j = 125^\circ C$		2.0	—	—	
	$V_{DS} = V_{GS}, I_D = 1.0mA, T_j = -55^\circ C$		—	—	—	
Gate to Source Leakage	$V_{GS} = \pm 20V, T_j = 25^\circ C$	I_{GSS}	—	10	±100	nA
	$V_{GS} = \pm 20V, T_j = 125^\circ C$		—	30	—	
Zero Gate Voltage Drain Current	$V_{DS} = -50V, V_{GS} = 0V, T_j = 25^\circ C$	I_{DSS}	—	—	-10	μA
	$V_{DS} = -50V, V_{GS} = 0V, T_j = 125^\circ C$		—	—	-750	
Forward Transconductance	$V_{DS} = -10V, I_D = -70A, T_j = 25^\circ C$	g_{fs}	—	70	—	Mho
	$V_{DS} = -10V, I_D = -70A, T_j = -40^\circ C$		40	85	—	
	$V_{DS} = -10V, I_D = -70A, T_j = 125^\circ C$		—	63	—	
Total Gate Charge	$V_{GS} = -10V$	Q_g	—	200	350	nC
Gate to Source Charge	$V_{DS} = -25V$	Q_{gs}	—	50	-	
Gate to Drain Charge	$I_D = -70A$	Q_{gd}	—	65	-	
Turn on Delay Time	$V_{GS} = -10V$	$t_{d(on)}$	—	30	45	nsec
Rise Time	$V_{DS} = -30V$	t_r	—	35	75	
Turn off Delay Time	$I_D = -50A$	$t_{d(off)}$	—	40	100	
Fall Time	$R_G = 1.0\Omega, pw = 3\mu s$	t_f	—	25	75	
Diode Forward Voltage	$I_F = -70A, V_{GS} = 0V$	V_{SD}	—	-	1.3	V
Diode Reverse Recovery Time	$I_F = -70A, di/dt = -100A/\mu s$	t_{rr}	—	55	250	nsec
Reverse Recovery Charge		Q_{rr}	—	60	—	nC
Input Capacitance	$V_{GS} = 0V$	C_{iss}	—	13,500	—	pF
Output Capacitance	$V_{DS} = 25V$	C_{oss}	—	1650	—	
Reverse Transfer Capacitance	$f = 1\text{ MHz}$	C_{rss}	—	650	—	

NOTE: All specifications are subject to change without notification.
 SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: FT0042A

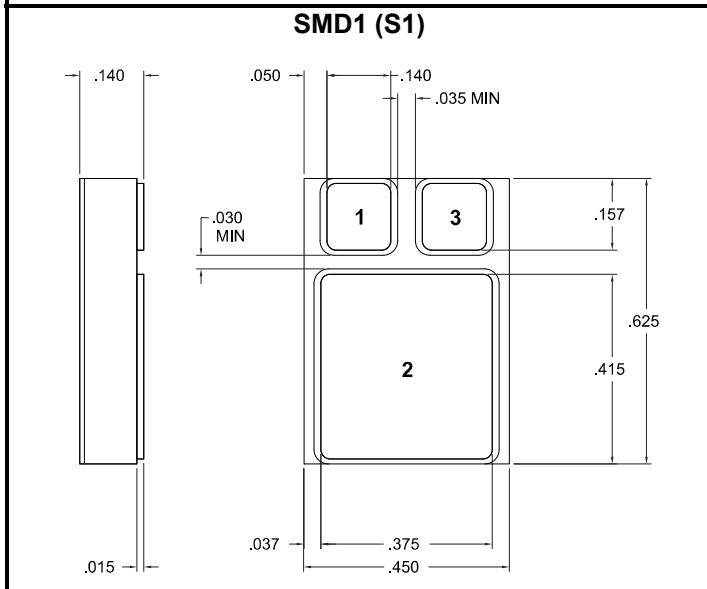
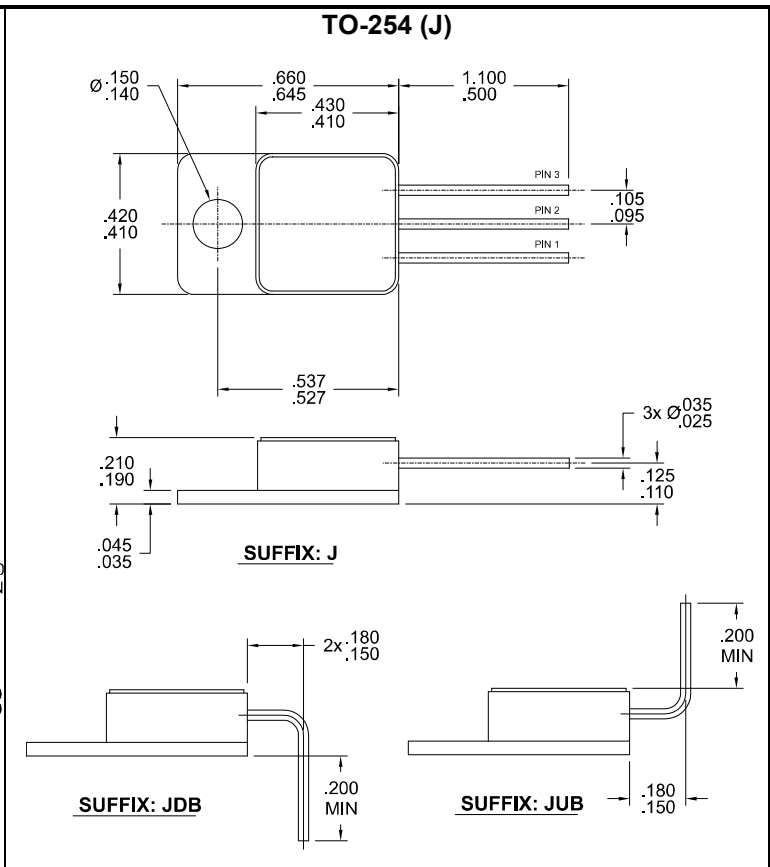
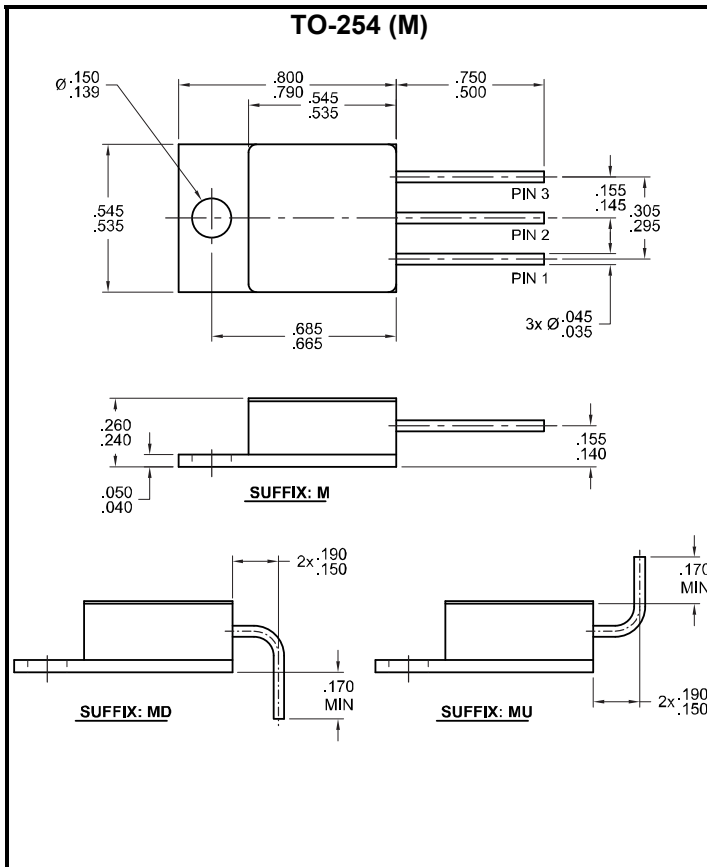
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PIN ASSIGNMENT (Standard)

Package	Drain	Source	Gate
TO-254 (M)	Pin 1	Pin 2	Pin 3
TO-257 (J)	Pin 1	Pin 2	Pin 3
SMD1 (S1)	Pin 2	Pin 1	Pin 3

Available Part Numbers:
 SFF110P05M, SFF110P05MDB, SFF110P05MUB,
 SFF110P05J, SFF110P05JDB, SFF110P05JUB,
 SFF110P05S1